

# RF Low Noise FET CE3521M4

# 20 GHz Low Noise FET in Dual Mold Plastic PKG

# **DESCRIPTION**

- Low Noise and High Gain
- Original Dual Mold Plastic package

# **FEATURES**

Low noise figure and high associated gain:
 NF = 0.70 dB TYP., Ga = 11.9 dB TYP.
 @V<sub>DS</sub> = 2 V, I<sub>D</sub> = 10 mA, f = 20 GHz

#### **PACKAGE**

Flat-lead 4-pin thin-type super minimold package



# **APPLICATIONS**

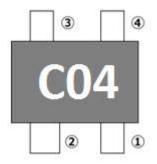
- DBS LNB gain-stage, Mix-stage
- Low noise amplifier for microwave communication systems

# ORDERING INFORMATION

Part Number	Order Number	Package	Marking	Description
CE3521M4	CE3521M4-C2	Flat-lead 4-pin	C04	Embossed tape 8 mm wide
		thin-type super		• Pin 1 (source), Pin 2 (drain)
		minimold		face the perforation side of
		package		the tape
				<ul> <li>MOQ 15 kpcs/reel</li> </ul>



# PIN CONFIGURATION AND INTERNAL BLOCK DIAGRAM



Pin No.	Pin Name
1	Source
2	Drain
3	Source
4	Gate

# **ABSOLUTE MAXIMUM RATINGS**

(TA = +25°C, unless otherwise specified)

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Parameter	Symbol	Rating	Unit		
Drain to Source Voltage	V <sub>DS</sub>	4.0	V		
Gate to Source Voltage	$V_{GS}$	-3.0	V		
Drain Current	I <sub>D</sub>	I <sub>DSS</sub>	mA		
Gate Current	I <sub>G</sub>	80	μΑ		
Total Power Dissipation	P <sub>tot</sub>	125	mW		
Channel Temperature	T <sub>ch</sub>	+150	°C		
Storage Temperature	T <sub>stg</sub>	-55 to +125	°C		
Operation Temperature	T <sub>op</sub>	-55 to +125 <sup>Note</sup>	°C		

Note Refer to Total Power Dissipation vs. Ambient Temperature graph on page 4

# RECOMMENDED OPERATING RANGE

 $(TA = +25^{\circ}C. \text{ unless otherwise specified})$ 

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Parameter	Symbol	MIN.	TYP.	MAX.	Unit
Drain to Source Voltage	V <sub>DS</sub>	+1	+2	+3	V
Drain Current	I <sub>D</sub>	5	10	15	mA



# **ELECTRICAL CHARACTERISTICS**

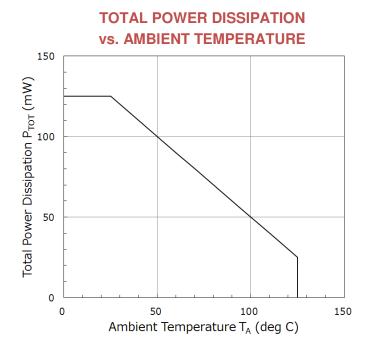
(TA = +25°C, unless otherwise specified)

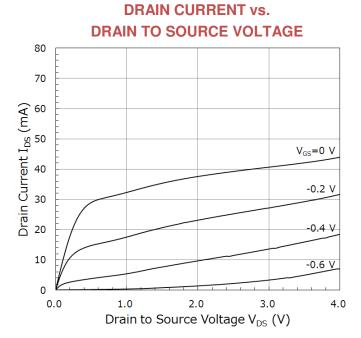
Parameter	Symbol	Condition	MIN.	TYP.	MAX.	Unit
Gate to Source Leak Current	I <sub>GSO</sub>	V <sub>GS</sub> = -3.0V	1	0.4	10	μΑ
Saturated Drain Current	I <sub>DSS</sub>	$V_{DS} = 2V$ , $V_{GS} = 0V$	23	40	57	mA
Gate to Source Cut-off Voltage	$V_{\text{GS(off)}}$	$V_{DS} = 2V, I_D = 100 \mu A$	-1.10	-0.75	-0.39	٧
Transconductance	Gm	$V_{DS} = 2V$ , $I_D = 10mA$	47	62	-	mS
Noise Figure	NF	$V_{DS} = 2V, I_{D} = 10mA,$	-	0.70	1.05	dB
Associated Gain	Ga	f = 20GHz	9.9	11.9	-	dB

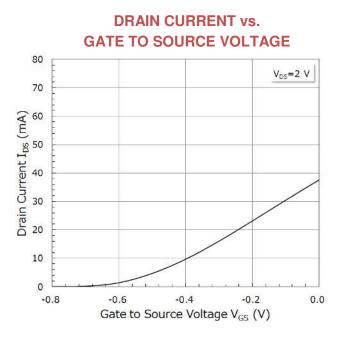


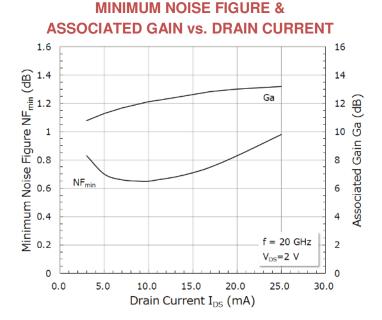
# **TYPICAL CHARACTERISTICS:**

(TA=+25°C, unless otherwise specified)











# **S-PARAMETERS**

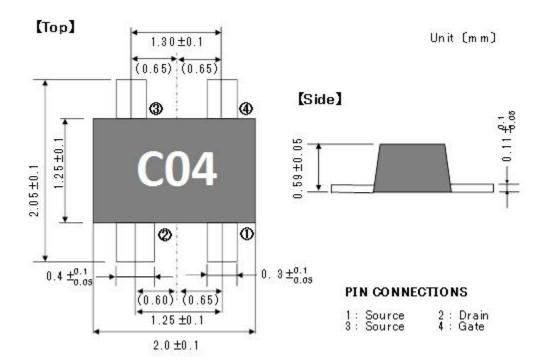
S-Parameters are available on the CEL web site.

# RECOMMENDED SOLDERING CONDITIONS

Recommended Soldering Conditions are provided on the CEL web site.

# **PACKAGE DIMENSIONS**

Flat-lead 4-pin thin-type super minimold package





# **REVISION HISTORY**

Version	Change to current version	Page(s)
CDS-0020-03 (Issue A)	Initial datasheet	N/A
February 19, 2016		
CDS-0020-03 (Issue B)	Updated Marking Information	1, 2, 3
April 27, 2016		
CDS-0020-04 (Issue A)	Updated Specs in "Absolute Maximum Ratings" Table	2, 4, 5
July 29, 2016	Added "Typical Characteristics" section (graphs)	
	Added "S-Parameters" and "Recommended Soldering	
	Conditions" sections	



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#### [CAUTION]

This product uses gallium arsenide (GaAs) of the toxic substance appointed in laws and ordinances. GaAs vapor and powder are hazardous to human health if inhaled or ingested.

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- Do not chemically make gas or powder with this product.
- When discarding this product, please obey the laws of your country.
- Do not lick the product or in any way allow it to enter the mouth.

#### [CAUTION]

Although this device is designed to be as robust as possible, ESD (Electrostatic Discharge) can damage this device. This device must be protected at all times from ESD. Static charges may easily produce potentials of several kilovolts on the human body or equipment, which can discharge without detection. Industry-standard ESD precautions should be used at all times.

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